

# **isc** Silicon NPN Power Transistor

# **BUX65**

## DESCRIPTION

- · High Collector-Emitter Sustaining Voltage-:V<sub>CEO(SUS)</sub>= 500V(Min.)
- · Fast Switching Speed
- · High Reliability
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

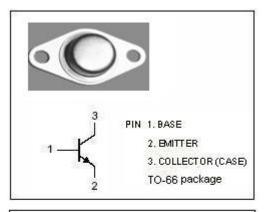
· Designed for use in high frequency and efficiency converters, switching regulators and motor control

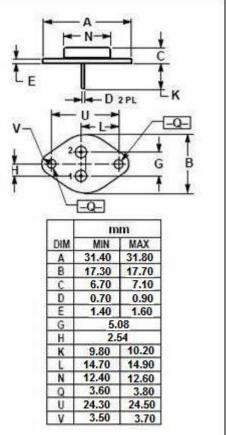
ABSOLUTE MAXIMUM RATINGS(T.=25°C)

ABSOLUTE MAAIMUM KATINGS $(1_a=25 C)$							
SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>CBO</sub>	Collector-Base Voltage	500	V				
V <sub>CEO</sub>	Collector-Emitter Voltage	500	V				
$V_{\text{EBO}}$	Emitter-Base Voltage	6	V				
lc	Collector Current-Continuous	3	А				
Pc	Collector Power Dissipation@Tc=25°C	70	W				
TJ	Junction Temperature	200	°C				
T <sub>stg</sub>	Storage Temperature	-65~200	°C				

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	3.0	°C/W







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## **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	500			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 0.1mA; I <sub>E</sub> = 0	500			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 0.1mA; I <sub>C</sub> = 0	6			v
V <sub>CE</sub> (sat)-1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			0.8	v
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.3A			1.5	v
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			1.0	v
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V; I <sub>E</sub> = 0			100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			100	μA
hfe	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	20		80	
fī	Current-Gain—Bandwidth Product	I <sub>C</sub> =0.5A;V <sub>CE</sub> =10V	8			MHz

### **NOTICE:**

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